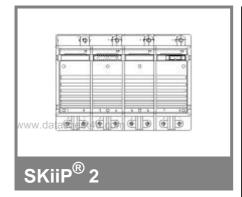
SKiiP 232GDL120-4DU



7-pack - integrated intelligent Power System

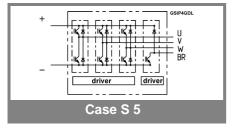
Power section - 3 phase bridge SKiiP 232GDL120-4DU

Features

- . SKiiP technology inside
- CAL diode technology
- Integrated current sensor
- Integrated temperature sensor
- Integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 2 System)
- IEC 60068-1 (climate) 40/125/56
- UL recognized file no. E63532
- with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)

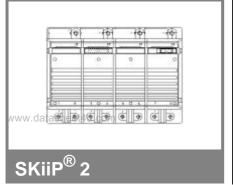
Absolute Maximum Ratings		s = 25 °C unless otherwise specified				
Symbol	Conditions	Values	Units			
IGBT						
V_{CES}		1200	V			
V _{CES} V _{CC} 1)	Operating DC link voltage	900	V			
V_{GES}		± 20	V			
I _C	T _s = 25 (70) °C	200 (150)	Α			
Inverse diode						
$I_F = -I_C$	T _s = 25 (70) °C	200 (150)	Α			
I _{FSM}	$T_j = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}; \text{sin}.$	1440	Α			
I ² t (Diode)	Diode, T _j = 150 °C, 10 ms	10	kA²s			
T_j , (T_{stg})		- 40 (- 25) + 150 (125)	°C			
V _{isol}	AC, 1 min. (mainterminals to heat sink)	3000	V			

	I							
Characteristics T _s = 25 °C unless otherwise specified								
Symbol	Conditions				min.	typ.	max.	Units
IGBT						-7 [
V _{CEsat}	I _C = 175 A,	T _i = 25 (1	25) °C			2,6 (3,1)	3,1	V
V _{CEO}	T _i = 25 (125		,			1,2 (1,3)	1,5 (1,6)	V
r _{CE}	T _i = 25 (125) °C					7,5 (10)	9 (11,5)	mΩ
I _{CES}	$V_{GE} = 0 \text{ V}, V_{CE} = V_{CES},$				(10)	0,4	mA	
	$T_i = 25 (125)$	5) °C						
E _{on} + E _{off}	I _C = 175 A,	V _{CC} = 60	0 V				53	mJ
	T _j = 125 °C	, V _{CC} = 90	00 V				93	mJ
R _{CC' + EE'}	terminal chi	p, T _i = 12	5 °C			0,5		mΩ
L _{CE}	top, bottom					15		nH
C _{CHC}	per phase,	AC-side				1,4		nF
Inverse o	diode							
$V_F = V_{EC}$	I _F = 150 A,	T _i = 25 (1	25) °C			2,1 (1,9)	2,6	V
V_{TO}	$T_j = 25 (125)$					1,3 (1)	1,4 (1,1)	V
r _T	$T_j = 25 (125)$					5 (6)	6,8 (7,8)	mΩ
E _{rr}	$I_{\rm C} = 175 {\rm A},$						6	mJ
	T _j = 125 °C	$V_{CC} = 90$	00 V				8	mJ
Mechani	cal data							
M_{dc}	DC termina	-			6		8	Nm
M _{ac}	AC terminals, SI Units				13		15	Nm
W	SKiiP® 2 System w/o heat sink					3,5		kg
W	heat sink					8,5		kg
Thermal	character	istics (P16 hea	t sink; 27	75 m³/h)	; " _r " refer	ence to	
	ture sense	or			I		0.400	14004
R _{th(j-s)I}	per IGBT						0,129	K/W
R _{th(j-s)D}	per diode						0,375	K/W
R _{th(s-a)}	per module		\			•	0,036	K/W
Z_{th}	R _i (mK/W) (max. valu 2	ues) 3	4	l 1	tau 2	_i (s) 3	4
7	14	2 99	ა 15	0	1	2 0,13	0,001	4 1
Z _{th(j-r)I}	41	289	45	0	'1	0,13	0,001	1
Z _{th(j-r)D}	1,7	24	7,6	2,6	494	165	20	0,03
$Z_{th(r-a)}$	1,1	4	ι,υ	۷,0	734	100	20	0,03



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SKiiP 232GDL120-4DU



Absolute Maximum Ratings		T _a = 25 °C unless otherwise specified		
Symbol	Conditions	Values	Units	
V_{S1}	stabilized 15 V power supply	18	V	
V_{S2}	unstabilized 24 V power supply	30	V	
V_{iH}	input signal voltage (high)	15 + 0,3	V	
dv/dt	secondary to primary side	75	kV/μs	
V_{isollO}	input / output (AC, r.m.s., 2s)	3000	Vac	
V _{isol12}	output 1 / output 2 (AC, r.m.s., 2s)	1500	Vac	
f _{sw}	switching frequency	20	kHz	
f _{out}	output frequency for I=I _C ;sin.	1	kHz	
$T_{op} (T_{stg})$	operating / storage temperature	- 40 + 85	°C	

7-pack - integrated intelligent Power System

7-pack integrated gate driver - 3 phase bridge SKiiP 232GDL120-4DU

Gate driver features

- · CMOS compatible inputs
- Wide range power supply
- Integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- Short circuit protection
- · Over current protection
- Over voltage protection (option)
- Power supply protected against under voltage
- · Interlock of top/bottom switch
- Isolation by transformer
- IEC 60068-1 (climate) 40/85/56

Characteristics (T _a					= 25 °C)
Symbol	Conditions	min. typ.		max.	Units
V_{S1}	supply voltage stabilized	14,4	15	15,6	V
V_{S2}	supply voltage non stabilized	20	24	30	V
I _{S1}	V _{S1} = 15 V	410+390	410+390*f/f _{max} +3,6*(I _{AC} /A)		
I _{S2}	V _{S2} = 24 V	300+280*f/f _{max} +2,6*(I _{AC} /A)			mA
V_{iT+}	input threshold voltage (High)			12,3	V
V_{iT-}	input threshold voltage (Low)	4,6			V
R _{IN}	input resistance		10		kΩ
t _{d(on)IO}	input-output turn-on propagation time			1,5	μs
t _{d(off)IO}	input-output turn-off propagation time			1,4	μs
tpERRRESET	error memory reset time	9			μs
t _{TD}	top / bottom switch : interlock time		2,3		μs
I _{analogOUT}	8 V corresponds to max. current of 15 V supply voltage		200		
L	(available when supplied with 24 V)			50	mA
I _{Vs1outmax} I _{A0max}	output current at pin 13/20/22/24/26			5	mA
V _{0I}	logic low output voltage			0,6	V
V _{0H}	logic high output voltage			30	V
I _{TRIPSC}	over current trip level (I _{analog OUT} = 10 V)		250		Α
I _{TRIPLG}	ground fault protection		58		Α
T _{tp}	over temperature protection	110		120	°C
U _{DCTRIP}	trip level of U _{DC} -protection	900			V
	(U _{analog OUT} = 9 V); (option)				

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